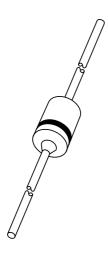
# **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# **BYD13 series**Controlled avalanche rectifiers

Product specification
Supersedes data of April 1992
File under Discrete Semiconductors, SC01

1996 May 24



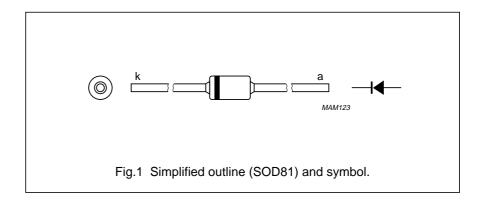


# Controlled avalanche rectifiers

## **BYD13 series**

#### **FEATURES**

- · Glass passivated
- High maximum operating temperature
- · Low leakage current
- · Excellent stability
- Guaranteed avalanche energy absorption capability
- Available in ammo-pack.



#### **DESCRIPTION**

Cavity free cylindrical glass package through Implotec<sup>™(1)</sup> technology.

This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.

#### (1) Implotec is a trademark of Philips.

#### **MARKING**

TYPE NUMBER	MARKING CODE
BYD13D	13D PH
BYD13G	13G PH
BYD13J	13J PH
BYD13K	13K PH
BYD13M	13M PH

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>RRM</sub>	repetitive peak reverse voltage				
	BYD13D		_	200	V
	BYD13G		_	400	V
	BYD13J		_	600	V
	BYD13K		_	800	V
	BYD13M		_	1000	V
V <sub>RWM</sub>	crest working reverse voltage				
	BYD13D		_	200	V
	BYD13G		_	400	V
	BYD13J		_	600	V
	BYD13K		_	800	V
	BYD13M		_	1000	V
V <sub>R</sub>	continuous reverse voltage				
	BYD13D		_	200	V
	BYD13G		_	400	V
	BYD13J		_	600	V
	BYD13K		_	800	V
	BYD13M		_	1000	V

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SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>F(AV)</sub>	average forward current	T <sub>tp</sub> = 55 °C; lead length = 10 mm; averaged over any 20 ms period; see Figs 2 and 4	_	1.40	А
		T <sub>amb</sub> = 65 °C; PCB mounting (see Fig.9); averaged over any 20 ms period; see Figs 3 and 4	_	0.75	A
I <sub>FSM</sub>	non-repetitive peak forward current	t = 10 ms half sinewave; $T_j = T_{j \text{ max}}$ prior to surge; $V_R = V_{RRMmax}$	_	20	А
E <sub>RSM</sub>	non-repetitive peak reverse avalanche energy	L = 120 mH; $T_j = T_{j \text{ max}}$ prior to surge; inductive load switched off	_	7	mJ
T <sub>stg</sub>	storage temperature		-65	+175	°C
T <sub>j</sub>	junction temperature	see Fig.5	-65	+175	°C

#### **ELECTRICAL CHARACTERISTICS**

 $T_i = 25$  °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>F</sub>	forward voltage	$I_F = 1 \text{ A}$ ; $T_j = T_{j \text{ max}}$ ; see Fig.6	_	_	0.93	V
		I <sub>F</sub> = 1 A; see Fig.6	_	_	1.05	V
$V_{(BR)R}$	reverse avalanche breakdown voltage	I <sub>R</sub> = 0.1 mA				
	BYD13D		225	_	_	V
	BYD13G		450	_	_	V
	BYD13J		650	_	_	V
	BYD13K		900	_	_	V
	BYD13M		1100	_	_	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = V <sub>RRMmax</sub> ; see Fig.7	_	_	1	μΑ
		V <sub>R</sub> = V <sub>RRMmax</sub> ; T <sub>j</sub> = 165 °C; see Fig.7	_	_	100	μΑ
t <sub>rr</sub>	reverse recovery time	when switched from $I_F = 0.5$ A to $I_R = 1$ A; measured at $I_R = 0.25$ A; see Fig.10	_	3	_	μs
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 0 V; f = 1 MHz; see Fig.8	_	21	-	pF

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-tp</sub>	thermal resistance from junction to tie-point	lead length = 10 mm	60	K/W
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	120	K/W

#### Note

1. Device mounted on epoxy-glass printed-circuit board, 1.5 mm thick; thickness of copper  $\geq$ 40  $\mu$ m, see Fig.9. For more information please refer to the "General Part of Handbook SC01".

# Controlled avalanche rectifiers

## BYD13 series

#### **GRAPHICAL DATA**

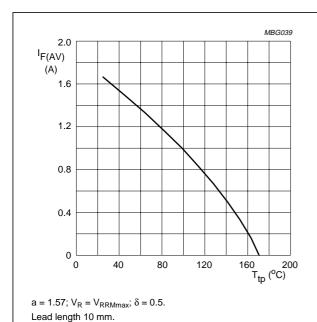


Fig.2 Maximum permissible average forward current as a function of tie-point temperature (including losses due to reverse leakage).

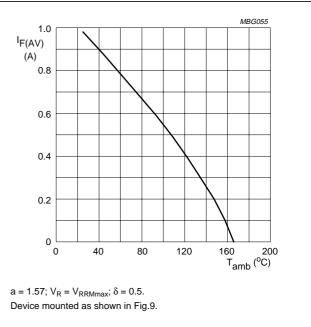


Fig.3 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).

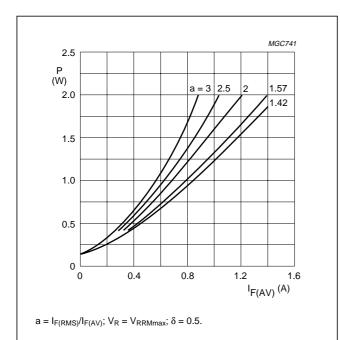


Fig.4 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.

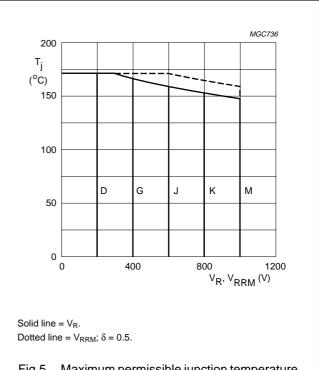
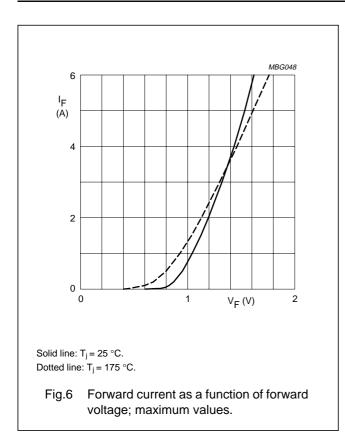


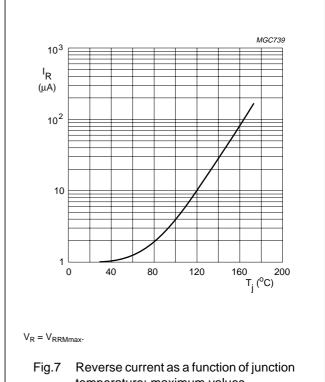
Fig.5 Maximum permissible junction temperature as a function of reverse voltage.

Product specification Philips Semiconductors

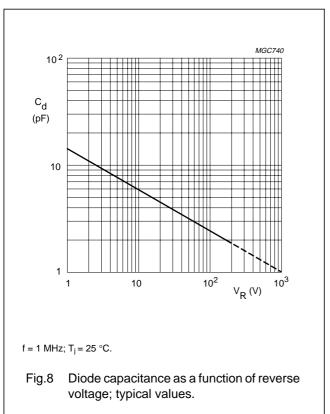
# Controlled avalanche rectifiers

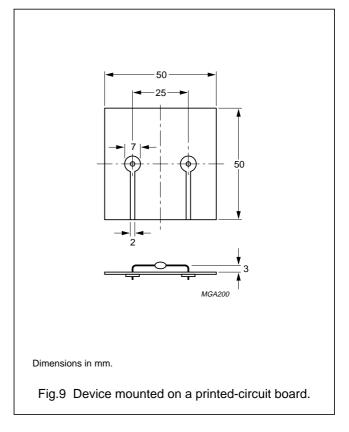
# BYD13 series





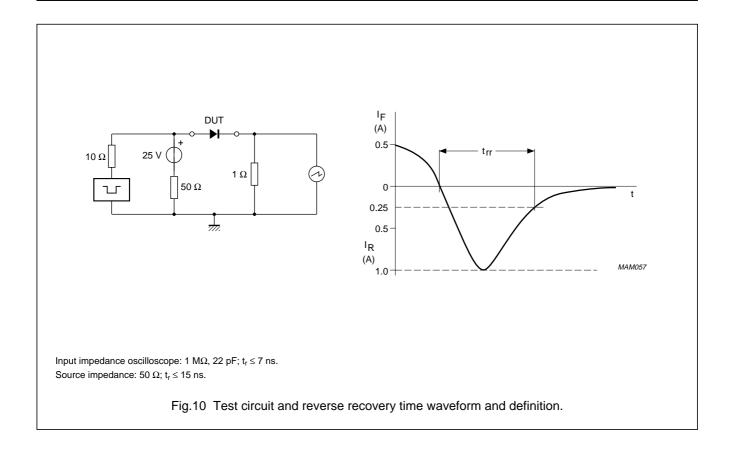
temperature; maximum values.





# Controlled avalanche rectifiers

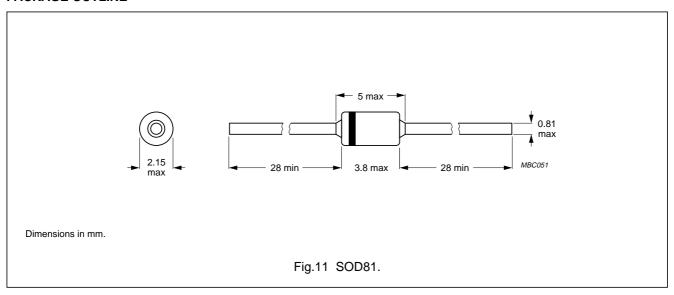
# BYD13 series



# Controlled avalanche rectifiers

BYD13 series

#### **PACKAGE OUTLINE**



#### **DEFINITIONS**

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting and a second	

#### **Limiting values**

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

#### LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.